Comparisons Between Ripple-Carry Adder and Carry-Look-Ahead Adder

Comparing Propagation Delays and Power Dissipation on CMOS-simulated Circuits in HSPICE

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Abstract — A four-bit adder is simulated using HSPICE in two classic design methods: a ripple-carry adder (RCA) and a carry-look-ahead adder (CLA). All components of the adders are composed of PMOS, NMOS, and capacitors. The propagation delay and power dissipation were measured under different VDD values and different operating temperatures in HSPICE. A comparison of these two metrics were analyzed between the RCA and CLA, and concludes that both the CLA and RCA operates optimally at low temperatures and are unsuitable for high VDD environments, CLA is preferred for faster computation while RCA is preferred for smaller chip size, and the CLA is preferred for high-frequency adder usage situations, and the CLA is more suitable for low-VDD systems.

Index Terms—CMOS, HSPICE, Ripple-Carry Adder, RCA, Carry-Look-Ahead Adder, CLA, Power Dissipation, Propagation Delay

I. INTRODUCTION

THE adder is a central component of a central processing unit of a computer. One of the main considerations of designing a digital circuits is the trade-off between size, performance speed, and power consumption. The RCA and CLA have differing designs, and thus different benchmarks for the above stated characteristics. This paper will be using HPICE to simulate and analyze the propagation delay and power dissipation of the RCA and CLA to explore and conclude which adder design is optimal under certain situations.

II. CMOS COMPONENTS DESIGN

Each transistor of the adders are composed of logic gates, and each logic gate is composed of CMOS components. Each gate used in this paper's design has been implemented at the CMOS level in HSPICE.

A. Design Constant Parameters

Each logic gates used in the adder design are composed of PMOS's, NMOS's, and capacitors. The major parameter constants are as follows: The length of all CMOS components are 45 nano-meters; the width of all NMOS transistors are 180 nano-meters; the width of all PMOS transistors are 360 nano- meters. The capacitors in the RCA are set at 0.1 picofarads; the capacitors in the CLA are set at 10 femto-farads. The CMOS is simulated using a Predictive Technology Model of a high performance 45 nano-meters metal gates. A full list of the parameters used for this paper's CMOS design is given in *Appendix A*.

B. Interver

The inverter is designed using one NMOS and one PMOS. Refer to *Appendix B* for the schematic of the inverter.

C. NAND and AND Gates

For an *n*-input NAND gate, the gate is designed using n NMOS's and n PMOS's. Each PMOS is connected in series and each NMOS is connected in parallel. Each gate input line is connected to one PMOS and one NMOS. The AND gate is implemented by adding an inverter at the output of the NAND gate. The full schematic of the 2-input NAND and AND gate is given in *Appendix B*.

D. NOR and OR Gates

For an *n*-input NOR gate, the gate is designed using n NMOS's and n PMOS's. Each PMOS is connected in parallel and each NMOS is connected in series. Each gate input is connected to one PMOS and one NMOS. The OR gate is implemented by adding an inverter at the output of the NOR gate. The full schematic of the 2-input NOR and OR gate is given in *Appendix B*.

E. XOR Gate

Both the RCA and CLA uses a two-input XOR gate. The XOR gate is designed using four NMOS's and four PMOS's. Each input to the NMOS or PMOS is either the gate-input itself or the gate-input inverted via an inverter. Gate input combinations that are supposed to yield a high signal are put on the PMOS side, and input combinations that are supposed to yield a low singer are put on the NMOS side. The full schematic of the XOR gate is given in *Appendix B*.

III. RIPPLE-CARRY ADDER DESIGN

The sub-units of an RCA is a full-adder. A full-adder takes in two one-bit numbers as well as a carry-in bit, and outputs the corresponding one-bit sum as well as a carry-out bit.

A. Half-Adder

The half-adder is a sub-component of the full-adder. The half-adder has two inputs: two one-bit digits denoted as A_H and B_H ; the half-adder has two outputs: a one-bit sum denoted as S_H and a one-bit carry-out denoted as C_H . The outputs are generated using an XOR gate and an AND gate(1). The full schematic of the half-adder is given in Appendix B.

$$S_H = A_H \oplus B_H \tag{1}$$
$$C_H = A_H \cdot B_H$$

B. RCA Full-Adder

The full-adder has three inputs: two one-bit digits denoted as A_{RF} and B_{RF} and a one-bit carry-in denoted as CIN_{RF} ; the full-adder has two outputs: a one-bit sum denoted as S_{RF} and a one-bit carry-out denoted as $COUT_{RF}$. The outputs are generated using a half-adder, an XOR gate, an AND gate, and an OR gate (2).The full schematic design of the full-adder is given in *Appendix B*.

$$A_{H} = A_{RF}$$

$$B_{H} = B_{RF}$$

$$S_{F} = S_{H} \oplus CIN_{RF}$$

$$OUT_{RF} = COUT_{H} + (S_{H} \cdot CIN_{RF})$$
(2)

C. Four-Bit RCA

C

The four-bit RCA has nine inputs: two four-bit binary numbers denoted as $A_R[3:0]$ and $B_R[3:0]$ along with a one-bit carry-in denoted as CIN_R ; the RCA has five outputs: a four-bit sum denoted as $S_R[3:0]$ along with a one-bit carry-out denoted as $COUT_R$. The RCA is constructed by concatenating multiple full-adders in series by connecting the carry-out bit of one full-adder to the next successive fulladder's carry-in bit. The carry-in bit of the RCA is connected to the carry-in line of the least significant full-adder's carry-in bit; similarly, the carry-out bit of the RCA is connected to the carry-out line of the most-significant full-adder's carry-out bit. Capacitors with a capacitance of 0.1 pico-farads are connected to each of the sum-bits as well as the carry-out bit. Refer to *Fig. 1* for the outline schematic of the RCA. The full HSPICE implementation of the four-bit RCA is given in *Appendix C*.

D. RCA Correctness

To test for the correctness of the implemented RCA, two test cases were run for correctness. *Table I* displays the test cases, expected results, and the actual results from the RCA adder simulated in CosmosScope. The CosmosScope waveform results of the test cases are given in *Appendix D*.

IV. CARRY-LOOK-AHEAD ADDER DESIGN

For the CLA, the carry-in bits of each adder component do not have wait for the pervious adder to compute the carryout bit. This can be achieved by determining each carry-in bit from the cumulation of the CLA's inputs as well as the



Fig. 1. Figure of the schematic layout of a RCA demonstrating the concatenation of the full adders

TABLE I RCA Correctness Test Cases and Results

	Input		Expected		Actual		
Test	Α	В	CIN	S	COUT	S	COUT
1	1111	0001	0	0000	1	0000	1
2	1110	0001	0	1111	0	1111	0

previous calculations in determining the other carry-in bits. More formally, instead of producing a carry-out bit for each adder, we produce a generating and propagating carries used to determine the successive carry-in bits.

A. Generating Carry

The generating carry for the i^{th} bit is produced from the AND of the two i^{th} input of the adder (3).

$$G_i = A_i \cdot B_i \tag{3}$$

B. Propagating Carry

The propagating carry for the i^{th} bit is produced from the OR of the two i^{th} input of the adder (4).

$$P_i = A_i + B_i \tag{4}$$

C. CLA Carries

The CLA's $i+1^{th}$ carry-in is generated by (5). Note that the i^{th} carry expand into the previous bit's carries. The carry-in for the least significant bit is CIN.

$$C_{i+1} = G_i + (P_i \cdot C_i) \tag{5}$$

Thus for the four-bit CLA implemented in this paper, the carry-in bits for the CLA are generated using equation (6).

$$CIN_0 = CIN$$

$$CIN_1 = G_0 + (P_0 \cdot C_0)$$

$$CIN_2 = G_1 + (P_1 \cdot C_1)$$

$$CIN_3 = G_2 + (P_2 \cdot C_2)$$
(6)



Fig. 2. Figure of the schematic layout of the CLA demonstrating the CLA full adders with the generating and propagating carry logic.

D. CLA Full-Adder

The CLA's full-adder has three inputs: two one-bit digits denoted as A_{CF} and B_{CF} and a one-bit carry-in denoted as CIN_{CF} ; the full-adder has three outputs: a one-bit sum produced by the XOR of A_{CF} , B_{CF} , and CIN_{CF} denoted as S_{CF} , a generating carry by using (4) denoted as G_{CF} , and a propagating carry by using (5) denoted as P_{CF} (7). The full schematic of the CLA is given in Appendix B.

$$S_{CF} = A_{CF} \oplus B_{CF} \oplus CIN_{CF}$$

$$G_{CF} = A_{CF} \cdot B_{CF}$$

$$P_{CF} = A_{CF} + B_{CF}$$
(7)

E. Fout-Bit CLA

The four-bit CLA has nine inputs: two four-bit binary numbers denoted as $A_C[3:0]$ and $B_C[3:0]$ along with a one-bit carry-in denoted as CIN_C ; the CLA has five outputs: a fourbit sum denoted as $S_C[3:0]$ along with a one-bit carry-out denoted as $COUT_C$. Each generating and propagating carries from each full-adder contribute to generate the successive carry-in bits. Capacitors with a capacitance of 10 femto-farads are connected to each of the sum-bits as well as the carry-out bits. Refer to Fig. 2 for the outline schematic design. The full HSPICE implementation of the four-bit CLA can be found in Appendix C.

F. CLA Correctness

To test for the correctness of the implemented CLA, two test cases were run for correctness. *Table II* displays the test cases, expected results, and the actual results from the CLA adder simulated in CosmosScope. The CosmosScope waveform results of the test cases are given in *Appendix D*.

TABLE II CLA CORRECTNESS TEST CASES AND RESULTS

	Input		Expected		Actual		
Test	Α	B	CIN	S	COUT	S	COUT
1	1111	0001	0	0000	1	0000	1
2	1110	0001	0	1111	0	1111	0

TABLE III LOW-TO-HIGH PROPAGATION DELAY OF CRITICAL PATH RESULTS OF THE RCA AND CLA IN NANO-SECONDS

Addor	VDD (Volts)	Temperature (Celcius)			
Auuci	VDD (Volts)	0	25	90	
	0.6	1.037	1.183	1.668	
RCA	0.9	0.313	0.354	0.510	
	1.8	0.256	0.225	0.250	
	0.6	0.389	0.426	0.543	
CLA	0.9	0.129	0.145	0.194	
	1.8	0.206	0.209	0.215	

TABLE IV High-to-Low Propagation Delay of Critical Path Results of the RCA and CLA in Nano-Seconds

Addon	VDD (Volts)	Temperature (Celcius)			
Auuei	VDD (Volts)	0	25	90	
	0.6	1.121	1.248	1.632	
RCA	0.9	0.403	0.443	0.585	
	1.8	0.114	0.123	0.255	
	0.6	0.544	0.607	0.774	
CLA	0.9	0.186	0.211	0.281	
	1.8	0.011	0.010	0.008	

V. PROPAGATION DELAY

In order to analyze the propagation delay differences between the RCA and the CLA, the propagation delays of the critical path of both designs will be used for the analysis. The critical path is from the *CIN* to the *COUT* for both fourbit adders. Both low-to-high (t_{pLH}) and high-to-low (t_{pHL}) propagation delays will be analyzed. Propagation delay will be measured at temperatures 0 Celsius, 25 Celsius, and 90 Celsius, as well as at voltage supply values 0.6 volts, 0.9 volts, and 1.8 volts.

A. Low-to-High Propagation Delay

To trigger a low-to-high signal change in COUT, input A[3:0] is set at 1111 and B[3:0] is set at 0000, and the CIN signal will change from 0 to 1. This way the sum changes from 1111 to 0000 and the COUT from 0 to 1. Table III presents the findings of the low-to-high propagation delay results.

B. High-to-Low Propagation Delay

To trigger a high-to-low signal change in COUT, input A[3:0] is set at 1111 and B[3:0] is set at 0000, and the CIN signal will change from 1 to 0. This way the sum changes from 0000 to 1111 and the COUT from 1 to 0. Table IV presents the findings of the propagation delay results.

C. Propagation Delay Estimation

The estimation of propagation delay (t_p) is the average of the low-to-high and high-to-low propagation delay(8).

$$t_p = \frac{t_{pLH} + t_{pHL}}{2} \tag{8}$$

Table V displays the propagation delay estimations of both the RCA and CLA in varying operating temperatures and *VDD* values.

TABLE V PROPAGATION DELAY ESTIMATIONS OF RCA AND CLA IN NANO-SECONDS

Adder	VDD (Volts)	Temperature (Celcius)			
Auuti		0	25	90	
RCA	0.6	1.079	1.216	1.650	
	0.9	0.358	0.399	0.548	
	1.8	0.185	0.174	0.238	
	0.6	0.467	0.517	0.659	
CLA	0.9	0.158	0.178	0.238	
	1.8	0.109	0.110	0.112	

VI. POWER DISSIPATION

Two main types of power dissipation are measured for this paper: static and dynamic power dissipation. The power dissipation will be measured with the product of the average current and the supply power (9). The time frame used to measure the average current will be defined in the following two sections.

$$P = I_{avg} \cdot V_{DD} \tag{9}$$

A. Dynamic Power Dissipation

Dynamic power dissipation (P_D) is a measurement of the average power dissipated over the time frame in which a signal rises or falls. Thus the time frame used to measure the average current will be between the start of a signal change, denoted as T_1 , and the end of the signal change, denoted as T_2 . Equation (10) describes the measurement of dynamic power dissipation.

$$P_D = \frac{\sum_{t=T_1}^{T_2} I(t)}{T_2 - T_1} \cdot V_{DD}$$
(10)

Determining T_1 and T_2 are done by analyzing the waveform in CosmosScope manually. Since it is not possible to determine the exact moment a signal change occurs, the time frame used for the final calculation will include an arbitrary small unit of time ϵ to the left of T_1 and to the right of T_2 in order to ensure the entirety of the signal change is encapsulated in the calculation (11). For this paper, the value of ϵ will be 0.01 micro-seconds.

$$P_D = \frac{\sum_{t=T_1-\epsilon}^{T_2+\epsilon} I(t)}{(T_2+\epsilon) - (T_1-\epsilon)} \cdot V_{DD}$$
(11)

Table V and Table VI displays the low-to-high (P_{DLH}) and high- to-low (P_{DHL}) dynamic power dissipation of the COUT signal in both the RCA and CLA.

B. Static Power Dissipation

Static power dissipation (P_S) is the measurement of the average power dissipated of an unchanging signal. Since the signal is unchanging, the time frame in which to measure static power dissipation can be chosen arbitrarily. In this paper the time frame will be the exact same length as those used to measure the dynamic power dissipation in order to open the potential of observations between dynamic and static power dissipation. *Table VII* and *Table VIII* displays the static power

TABLE VI Low-to-High Dynamic Power Dissipation in RCA and CLA in Micro-Watts

Addor	VDD (Volta)	Temperature (Celcius)			
Auuei	VDD (Volts)	0	25	90	
RCA	0.6	2.153	2.165	2.231	
	0.9	5.207	5.244	5.363	
	1.8	407.5	408.5	406.9	
CLA	0.6	0.535	0.553	0.653	
	0.9	1.780	1.859	2.129	
	1.8	595.1	590.9	586.8	

TABLE VII HIGH-TO-LOWS DYNAMIC POWER DISSIPATION IN RCA AND CLA IN MICRO-WATTS

Addon	VDD (Volta)	Temperature (Celcius)			
Audel	VDD (Volts)	0	25	90	
	0.6	7.712	7.696	7.695	
RCA	0.9	19.31	19.14	19.05	
	1.8	613.8	600.9	572.5	
	0.6	1.251	1.277	1.376	
CLA	0.9	5.224	5.085	5.090	
	1.8	766.2	743.3	700.0	

dissipation of both static-high (P_{SH}) and static-low (P_{SL}) voltage of the *COUT* signal in both the RCA and CLA.

C. Power Dissipation Estimation

The estimation of dynamic power dissipation is the average of the low-to-high and high-to-low power dissipation (12).

$$P_D = \frac{P_{DLH} + P_{DHL}}{2} \tag{12}$$

TABLE VIII STATIC-LOW POWER DISSIPATION IN RCA AND CLA IN NANO-WATTS

Addon	VDD (Valta)	Temperature (Celcius)			
Auuci	VDD (Volts)	0	25	90	
	0.6	8.843	17.97	84.98	
RCA	0.9	7.982	129.9	334.0	
	1.8	340900	342000	346300	
	0.6	15.63	29.97	127.6	
CLA	0.9	46.09	211.4	570.4	
	1.8	541400	540600	543700	

TABLE IX Static-High Dynamic Power Dissipation in RCA and CLA in Nano-Watts

Addor	VDD (Volte)	Temperature (Celcius)			
Auuei	VDD (Volts)	0	25	90	
	0.6	2.892	19.43	67.95	
RCA	0.9	49.20	83.44	291.7	
	1.8	387900	388500	393000	
	0.6	12.16	22.99	76.59	
CLA	0.9	94.85	144.8	418.7	
	1.8	529900	529700	533600	

TABLE X Dynamic Power Dissipation Estimations of RCA and CLA in Micro-Watts

Addor	VDD (Volte)	Temperature (Celcius)			
Auuei	VDD (Volts)	0	25	90	
	0.6	4.933	4.931	4.963	
RCA	0.9	12.26	12.19	12.21	
	1.8	510.7	504.7	489.7	
CLA	0.6	0.893	0.915	1.015	
	0.9	3.500	3.470	3.610	
	1.8	680.7	677.1	643.4	

TABLE XI STATIC POWER DISSIPATION ESTIMATIONS OF RCA AND CLA IN NANO-WATTS

Addon	VDD (Valta)	Temperature (Celcius)			
Auuti	VDD (Volts)	0	25	90	
	0.6	5.870	18.70	76.47	
RCA	0.9	28.60	106.7	312.9	
	1.8	364400	365250	369650	
	0.6	13.90	26.48	102.1	
CLA	0.9	70.50	178.1	494.6	
	1.8	535650	535150	538650	

Similarly, the estimation of static power dissipation is the average of the static-high and-static low power dissipation (13).

$$P_D = \frac{P_{DLH} + P_{DHL}}{2} \tag{13}$$

Table X and *Table XI* displays the power dissipation estimations of both the RCA and CLA in varying operating temperatures and *VDD* values.

VII. DISCUSSION

After implementing and running simulations of the RCA and CLA in HSPICE, a number of notable conclusions can be made from the data results. These are as follows:

A. Propagation Delay

The propagation delay between a signal change in CIN and the corresponding change of the COUT signal are affected in different ways by the temperature and value of VDD.

As the temperature increases, each transistor will experience a higher intrinsic resistance value, and therefore possibly result in the slower propagation delay time as the temperature increases. The exception to this trend is when *VDD* has a value of 1.8 volts. At this high of a voltage, changes in temperature seems to keep the propagation delay at the same relative value.

As the value of *VDD* increases, it has two effects on the propagation delay: (i) decrease the propagation delay and (ii) decrease the change of propagation delay when the temperature varies. Once again the exception to this trend is when the *VDD* has a value of 1.8 volts. This may be due to the size of the CMOS transistors and it not being able to handle such high of a voltage since during HSPICE simulations there were warnings indicating a *VDD* value of 1.8 volts may cause unexpected behaviors. The CLA has a notably less propagation delay than the RCA. In each corresponding comparison of the same temperature and VDD value, the CLA's performance speed trumps the RCA's. This is due to the significantly shorter critical path of the CLA compared to the critical path of the RCA. However the CLA's high performance comes at the cost of a larger chip size due to the extra logic needed to be implemented with the

B. Dynamic Power Dissipation

generating and propagating carries.

Both the RCA and the CLA increases in power dissipation linearly at a small rate as the temperature increases. However an increase to the *VDD* value will exponentially increase the power dissipation. From 0.6 volts to 1.8 volts there is an increase of two orders of magnitude. This applies to both the low-to-high and high-to-low dynamic power dissipation.

The CLA has notably less power dissipation for a *VDD* value of 0.6 and 0.9 volts. At 1.8 volts the CLA has a higher dissipation value. This means for low-*VDD* systems using the CLA benefits in both power dissipation and performance.

C. Static Power Dissipation

Both the RCA and CLA increases in power dissipation increases at a slight exponential as temperature increases. This increase is significantly greater than the increase dynamic power dissipation experiences as temperature changes. For increase in the VDD value, there is a great exponential increase in power dissipation as the *VDD* value increases. Between 0.6 and 1.8 volts, there is a five order of magnitude difference in the dissipation values.

At a *VDD* value of 1.8 volts, the static power dissipation value of both the RCA and the CLA are relatively similar. For a *VDD* value of 0.6 and 0.9 volts, RCA has considerably less power dissipation.

VIII. CONCLUSIONS

From the analysis of the data and discussion above, this paper makes five main conclusions: (i) both the RCA and CLA operates optimally at lower temperatures; (ii) both the RCA and the CLA are unsuitable for high VDD value environments due to the unpredictable propagation delay as well as the immense power dissipation at this VDD value; (iii) if performance in the key concern the CLA is the more suited architecture due to the better performance in propagation delay; (iv) if the implementation using the adder is expecting a large number of computations, then the CLA is recommended due to the lower dynamic power dissipation for both lowto- high and high-to-low, however if computation tasks are infrequent, then the RCA is recommended due to the lower static power dissipation for both static-low and static-high; and (v) the CLA is more suitable for low-VDD systems due to the lower power dissipation and faster performance.

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APPENDIX A HSPICE SIMULATION PARAMETERS

The following is the parameter file used for the HSPICE simulations used in this paper:

.model r	nmos nmos level:	= 54					
+version	= 4.0	binunit =	1	paramchk=	= 1	mobmod =	= 0
+capmod	= 2	igcmod =	1	igbmod =	= 1	geomod =	= 1
+diomod	= 1	rdsmod =	0	rbodymod=	= 1	rgatemod=	= 1
+permod	= 1	acnqsmod=	0	trnqsmod=	= 0		
	0.7		1 05 000		1 000		1 05 000
+tnom	= 2 / - 2 = 5 - 010	toxe =	1.250-009	toxp =	= 1e-009 = 50-009	toxm =	= 1.25e-009
+11	= 2.30-010	wl =	0	lln =	= Je-009 = 1	wln =	= 3.75e-009 = 1
+1w	= 0	WT =	0	lwn =	= 1	wwn =	= 1
+1w1	= 0	ww] =	0	xpart =	= 0	toxref =	= 1.25e-009
+x1 =	-20e-9			npare	Ŭ	0011101	1.200 000
+vth0	= 0.46893	k1 =	0.4	k2 =	= 0	k3 =	= 0
+k3b	= 0	w0 =	2.5e-006	dvt0 =	= 1	dvt1 =	= 2
+dvt2	= 0	dvt0w =	0	dvt1w =	= 0	dvt2w =	= 0
+dsub	= 0.1	minv =	0.05	voffl =	= 0	dvtp0 =	= 1e-010
+dvtp1	= 0.1	lpe0 =	0	lpeb =	= 0	xj =	= 1.4e-008
+ngate	= 1e+023	ndep =	3.24e+018	nsd =	= 2e+020	phin =	= 0
+cdsc	= 0	cdscb =	0	cdscd =	= 0	cit =	= 0
+VOII	= -0.13	niactor =	2.22	etau =	- 62 010	etab =	- 1 20 010
+ VID	0.55	uo =	170000		- 1	- uu	- 0.20-010
+a1	= 0	a2 =	1	b0 =	= 0	h1 =	= 0
+keta	= 0.04	dwa =	0	dwb =	= 0	pclm =	= 0.02
+pdiblc1	= 0.001	pdiblc2 =	0.001	pdiblcb =	= -0.005	drout =	= 0.5
+pvaq	= 1e-020	delta =	0.01	pscbel =	= 8.14e+008	pscbe2 =	= 1e-007
+fprout	= 0.2	pdits =	0.08	pditsd =	= 0.23	pditsl =	= 2300000
+rsh	= 5	rdsw =	155	rsw =	= 80	rdw =	= 80
+rdswmin	= 0	rdwmin =	0	rswmin =	= 0	prwg =	= 0
+prwb	= 0	wr =	1	alpha0 =	= 0.074	alphal =	= 0.005
+beta0	= 30	agidl =	0.0002	bgidl =	= 2.1e+009	cgidl =	= 0.0002
+egidl	= 0.8	aigbacc =	0.012	bigbacc =	= 0.0028	cigbacc =	= 0.002
+nigbacc	= 1	aigbinv =	0.014	bigbinv =	= 0.004	cigbinv =	= 0.004
+eigbinv	= 1.1	nigbinv =	3	aigc =	= 0.02	bigc =	= 0.0025
+cigc	= 0.002	algsd =	0.02	bigsd =	= 0.0025 - 1	cigsa =	= 0.002 - 1
+nigc	= 1	poxeage =	5	pigca =	= 1	ntox =	= 1
TAICIGI	- 12	xiciyz =	5				
+caso	= 1.1e-010	cado =	1.1e-010	capo =	= 2.56e-011	cadl =	= 2.653e-010
+cqsl	= 2.653e-010	ckappas =	0.03	ckappad =	= 0.03	acde =	= 1
+moin	= 15	noff =	0.9	voffcv =	= 0.02		
+ktl	= -0.11	kt11 =	0	kt2 =	= 0.022	ute =	= -1.5
+ual	= 4.31e-009	ubl =	7.61e-018	ucl =	= -5.6e-011	prt =	= 0
+at	= 33000						
+inoimod	= 1	tnoimod =	0				
+ icc	- 0 0001	jewe -	10-011	tewas -	- 10-010	nic -	- 1
+iithefwc	d = 0.0001	jjwj –	0 001		= 10	vibue =	= 1
+isd	= 0.0001	iswd =	1e-011	iswad =	= 1e-010	nid =	= 1
+ijthdfwc	d= 0.01	iithdrev=	0.001	bvd =	= 10	xibvd =	= 1
+pbs	= 1	cjs =	0.0005	mjs =	= 0.5	pbsws =	= 1
+cjsws	= 5e-010	mjsws =	0.33	pbswgs =	= 1	cjswgs =	= 3e-010
+mjswgs	= 0.33	pbd =	1	cjd =	= 0.0005	mjd =	= 0.5
+pbswd	= 1	cjswd =	5e-010	mjswd =	= 0.33	pbswgd =	= 1
+cjswgd	= 5e-010	mjswgd =	0.33	tpb =	= 0.005	tcj =	= 0.001
+tpbsw	= 0.005	tcjsw =	0.001	tpbswg =	= 0.005	tcjswg =	= 0.001
+xtis	= 3	xtid =	3				
Idmag	- 0	dmai –	0	dmda -	- 0	dmaat -	- 0
+ancg	= 0	anci =	0	anag =	- 0	ancgi =	= 0
+aw j	- 0	xgw =	0	XGI -	- 0		
+rsha	= 0.4	abmin =	1e-010	rbpb =	= 5	rbpd =	= 15
+rbps	= 15	rbdb =	15	rbsb =	= 15	ngcon =	= 1
*						5	
.model p	pmos pmos level :	= 54					
+version	= 4.0	binunit =	1	paramchk=	= 1	mobmod =	= 0
+capmod	= 2	igcmod =	1	igbmod =	= 1	geomod =	= 1
+diomod	= 1	rdsmod =	U	rbodymod=	= 1	rgatemod=	= 1
+permod	= 1	acnqsmod=	U	urnqsmod=	= U		
+tnom	= 27	toxe -	1 30-009	town -	= 1e-009	torm -	= 1 30-009
+dt.ox	= 3e-010	epsrox =	3.9	wint =	= 5e-009	lint =	= 3.75e-009
+11	= 0	wl =	0	11n =	= 1	wln =	= 1
+lw	= 0	ww =	0	lwn =	= 1	wwn =	= 1
+lwl	= 0	wwl =	0	xpart =	= 0	toxref =	= 1.3e-009
+x1 =	-20e-9			-			

+vth0 +k3b +dvt2 +dsub +dvtp1 +ngate +cdsc +voff +vfb +uc +a1 +keta +pdiblc1 +fprout +fprout +prwb +beta0 +egid1 +nigbacc +eigbinv		-0.49158 0 -0.032 0.1 0.05 1e+023 0 -0.126 0.55 0 0 -0.047 0.001 1e-020 0.2 5 0 0 30 0.8 1 1.1	k1 w0 dvt0w minv lpe0 ndep cdscb nfactor u0 vsat a2 dwg pdiblc2 delta pdiblc2 delta pdits rdsw rdsw rdsw rdsw rdsw ind pdits rdsw rdswink wr agidl aigbacc aigbinv nigbinv		0.4 2.5e-006 0 0.05 0 2.44e+018 0 2.1 0.02 150000 1 0 0.001 0.01 0.08 155 0 1 0.0002 0.002 0.012 0.014 3	k2 dvt0 dvt1w voffl lpeb nsd cdscd eta0 ua a0 b0 dwb pdiblcb pscbe1 pditsd rsw rswmin alpha0 bgjdl bigbacc bigbinv aigc		-0.01 1 0 2e+020 0 2e-009 1 0 0 3.4e-008 8.14e+008 0.23 75 0 0.074 2.1e+009 0.0028 0.004 0.010687	k3 dvt1 dvt2w dvtp0 xj phin cit etab ub ags b1 pclm drout pscbe2 pdits1 rdw prwg alpha1 cgidl cigbacc cigbinv bigc		$\begin{array}{c} 0 \\ 2 \\ 0 \\ 1e-011 \\ 1.4e-008 \\ 0 \\ 0 \\ 0 \\ 5e-019 \\ 1e-020 \\ 0 \\ 0.12 \\ 0.56 \\ 9.58e-007 \\ 2300000 \\ 75 \\ 0 \\ 0.005 \\ 0.005 \\ 0.0002 \\ 0.002 \\ 0.004 \\ 0.0012607 \end{array}$
+cigc +nigc	=	0.0008	aigsd poxedge	=	0.010687	bigsd pigcd	=	0.0012607	cigsd ntox	=	0.0008 1
+xrcrg1	=	12	xrcrg2	=	5						
+cgso +cgsl +moin	=	1.1e-010 2.653e-010 15	cgdo ckappas noff	=	1.1e-010 0.03 0.9	cgbo ckappad voffcv	=	2.56e-011 0.03 0.02	cgdl acde	=	2.653e-010 1
+kt1 +ua1 +at	=	-0.11 4.31e-009 33000	ktll ubl	=	0 7.61e-018	kt2 uc1	=	0.022 -5.6e-011	ute prt	=	-1.5 0
+fnoimod	=	1	tnoimod	=	0						
+jss +ijthsfwd +jsd +ijshdfwd +pbs +cjsws +mjswgs +cjswgd +cjswgd +cjswgd +tjswg4 +tsis +dmcg +dwj		0.0001 0.01 0.001 1 5e-010 0.33 1 5e-010 0.005 3 0 0	jsws ijthsrew jswd ijthdrew cjs mjsws pbd cjswd tcjswd tcjsw xtid dmci xgw	= <i>J</i> = = = = = = = = =	1e-011 0.001 1e-011 0.0005 0.33 1 5e-010 0.33 0.001 3	jswgs bvs jswgd bvd mjs pbswgs cjd mjswd tpb tpbswg dmdg xgl		1e-010 10 1e-010 0.5 1 0.0005 0.33 0.005 0.005 0	njs xjbvs njd xjbvd pbsws cjswgs mjd pbswgd tcj tcjswg dmcgt		1 1 1 3e-010 0.5 1 0.001 0.001
+rshg +rbps	=	0.4 15	gbmin rbdb	=	1e-010 15	rbpb rbsb	=	5 15	rbpd ngcon	=	15 1

APPENDIX B CMOS AND ADDER COMPONENT SCHEMATICS

A. CMOS Implementation Schematic of an Inverter



B. CMOS Implementation Schematic of an NAND Gate





C. CMOS Implementation Schematic of an AND Gate

D. CMOS Implementation Schematic of an NOR Gate



E. CMOS Implementation Schematic of an OR Gate



F. CMOS Implementation Schematic of an XOR Gate



APPENDIX C RCA AND CLA HSPICE IMPLEMENTATION

A. Ripple-Carry Adder Implementation in HSPICE

*library setup

```
.include "45nm_HP.pm"
*define parameters
.param Supply = 0.9V *VDD supply voltage
* Defines VDD as global node
.global VDD
*** add voltage source for VDD
VDD VDD Gnd Supply
*****
* Inverter
.SUBCKT INV IN OUT
             VDD pmos l = 45n w = 360n
Gnd nmos l = 45n w = 180n
 m0 OUT IN VDD
m1 OUT IN Gnd
. ENDS
****
* NAND
.SUBCKT NAND A B OUT
 *** P-MOS
         VDD
 m0 OUT A
             VDD pmos 1 = 45n w = 360n
 m1 OUT B VDD VDD pmos 1 = 45n w = 360n
 *** NMOS
 m2 OUT A x Gnd nmos l = 45n w = 180n
m3 x B Gnd Gnd nmos l = 45n w = 180n
.ENDS
*****
* AND
******
* A --|
   | NAND | -- x -- | INV | -- OUT
*
* B --|
.SUBCKT AND A B OUT
 Xnand A B x NAND
 Xinv x OUT INV
.ENDS
*****
* XOR
*****
.SUBCKT XOR A B OUT
 *** A' ***
                      VDD pmos 1 = 45n w = 360n
 m0
     A_NOT
            А
                VDD
    A_NOT
 m2
                Gnd
                      Gnd nmos 1 = 45n w = 180n
            А
 *** B' ***
 m1 B_NOT
m3 B_NOT
            В
                VDD
                      VDD pmos 1 = 45n w = 360n
          ь
В
                      Gnd nmos 1 = 45n w = 180n
                Gnd
 *** XOR ***
 *** P-MOS
                      VDD pmos 1 = 45n w = 360n
           B_NOT
                VDD
 m4 w
                      VDD pmos 1 = 45n w = 360n
VDD pmos 1 = 45n w = 360n
                VDD
 m5
           B
     x
     OUT
 m6
           А
                W
                      VDD pmos 1 = 45n w = 360n
 m7
    OUT
           A_NOT
                х
 *** NMOS
           в у
                     Gnd nmos 1 = 45n w = 180n
 m8 OUT
         B_NOT z
                     Gnd nmos l = 45n w = 180n
 m9
     OUT
                   Gnd nmos 1 = 45n w = 180n
          A Gnd
 m10
     У
          A_NOT Gnd
                    Gnd nmos l = 45n w = 180n
 m11
     Z
ENDS
*****
* NOR
****
*** nmos ***
.SUBCKT NOR A B OUT
 m0 OUT A
m1 OUT B
                   Gnd nmos 1 = 45n w = 180n
               Gnd
 m1
     OUT
           В
               Gnd
                    Gnd nmos 1 = 45n w = 180n
```

*** p-mos ***

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m2 OUT В х VDD pmos 1 = 45n w = 360nm3 х A VDD VDD pmos 1 = 45n w = 360n .ENDS ***** * OR ***** * A --| * | NOR | -- x --| INV | -- OUT * B --| ****** .SUBCKT OR A B OUT Xnor A B x NOR Xinv x OUT INV .ENDS ***** * Half_Adder ***** A ----I | | XOR | ----- S B -----| | |--| AND | --- C |-* * * * * * * * * * * * * .SUBCKT HALF_ADDER A B S C Xxor A B S XOR Xand A B C AND .ENDS ***** * Full-Adder ***** ***** A ----I хI -S---x---| XOR |---S Cin| | Half_Adder | 1 B -----I ---с--у--хI Т | AND |---z Cin -----1 - 1 zΙ | OR |---COUT уI **** .SUBCKT FULL_ADDER A B CIN S COUT Xhalf_adder A B x y HALF_ADDER Xxor x CIN S XOR Xand x CIN z AND Xor yz COUT OR .ENDS ***** * 4-bit Full-Adder A0 -----I |---S0-----B0 -----| Half_Adder | ---COUT0---* CIN -----|_ A1 -----| ----S1-----B1 -----| Half_Adder ---COUT1---* COUT0----|_ A2 ----| |---S2-----B2 -----| Half_Adder | ---COUT2---* COUT1----|_ A3 -----| |---s3-----B3 -----| Half_Adder | |---COUT---* COUT2----|_ 1 *****

```
.SUBCKT RCA A0 A1 A2 A3 B0 B1 B2 B3 CIN S0 S1 S2 S3 COUT
 Xfull_adder0 A0 B0 CIN S0 COUT0 FULL_ADDER
Xfull_adder1 A1 B1 COUT0 S1 COUT1 FULL_ADDER
 Xfull_adder2 A2 B2 COUT1 S2 COUT2 FULL_ADDER
 Xfull_adder3 A3 B3 COUT2 S3 COUT FULL_ADDER
ENDS
*****
* Test that RCA gate is correct
*****
X4_bit_full_adder A0 A1 A2 A3 B0 B1 B2 B3 CIN S0 S1 S2 S3 COUT RCA
* Add capacitors
C0 S0 Gnd 0.1p
C1 S1 Gnd 0.1p
C2 S2 Gnd 0.1p
C3 S3 Gnd 0.1p
Ccout COUT Gnd 0.1p
* SYNTAX: V <name> <node1> <node2> pulse( <value1>, <value2>, <delay>,<rise time>, <fall time>, <ON time>, <period>)
*** define input signals for A and B PULSE
                                                               0.001u,
                                                                         7.999u,
          A0 Gnd pulse(0,
                                     0.9V,
     VA0
                                                     0.001u,
                                                                                   16u )
                                                ln,
                                              1n, 0.001u,
1n, 0.001u,
1n, 0.001u,
     VA1
           A1
                Gnd
                      pulse( 0,
                                      0.9V,
                                                               0.001u,
                                                                        7.999u,
                                                                                  16u
                                                               0.001u,
     VA2
                Gnd
                      pulse( 0,
                                     0.9V,
                                                                         7.999u,
           A2
                                                                                   16u
                                     0.9V,
     VA3
           A3
                Gnd
                      pulse( 0,
                                                               0.001u,
                                                                        7.999u,
                                                                                   16u
                                      0V,
0V,
                                              1n, 0.001u,
1n, 0.001u,
     VB0
                      pulse( 0.9V,
                                                                         7.999u,
           в0
                Gnd
                                                               0.001u,
                                                                                   16u
     VB1
           В1
                Gnd
                      pulse( 0.9V,
                                                               0.001u,
                                                                         7.999u,
                                                                                   16u
                                                     0.001u,
     VB2
           В2
                Gnd
                      pulse( 0.9V,
                                      0V,
                                               ln,
                                                               0.001u,
                                                                         7.999u,
                                                                                   16u
                                              1n, 0.001u,
     VB3 B3
                Gnd pulse( 0.9V,
                                      0V,
                                                               0.001u,
                                                                         7.999u,
                                                                                   16u )
     VCIN CIN Gnd pulse( 0.9V,
                                      0V,
                                               1n, 0.001u,
                                                              0.001u,
                                                                        3.999u,
                                                                                   8u )
* SYNTAX .TRAN <time step> <final time>
.TRAN 0.049u 17u
.MEASURE FALL_DELAY
 +TRIG V(CIN) VAL='Supply/2' FALL = 1
  +TARG V(COUT) VAL='Supply/2' FALL = 1
.MEASURE RISE DELAY
 +TRIG V(CIN) VAL='Supply/2' RISE = 2
 +TARG V(COUT) VAL='Supply/2' RISE = 2
* .MEASURE TRAN lowtohigh AVG i(VDD) FROM=3.99u TO=4.01u
* .MEASURE TRAN low AVG i(VDD) FROM=3.97u TO=3.99u
* .MEASURE TRAN hightolow AVG i(VDD) FROM=7.99u TO=8.01u
* .MEASURE TRAN high AVG i(VDD) FROM=7.97u TO=7.99u
* * .MEASURE TRAN supplycurrent AVG i(VDD) FROM=3.99u TO=4.01u
* .MEASURE TRAN lowtohighpower PARAM='-lowtohigh * 0.6' **0.6 is supply voltage
* .MEASURE TRAN lowpower PARAM='-low * 0.6' **0.6 is supply voltage
* .MEASURE TRAN hightolowpower PARAM='-hightolow * 0.6' **0.6 is supply voltage
* .MEASURE TRAN highpower PARAM='-high * 0.6' **0.6 is supply voltage
```

```
.TEMP 90
```

```
.OPTION Post
```

.end

B. Carry-Look-Ahead Adder Implementation in HSPICE

```
*library setup
.include "45nm_HP.pm"
*define parameters
.param Supply = 1.8V *VDD supply voltage
* Defines VDD as global node
.global VDD
*** add voltage source for VDD
VDD VDD Gnd Supply
*****
* Inverter
SUBCKT INV IN OUT
 m0 OUT IN VDD VDD pmos l = 45n w = 360n
m1 OUT IN Gnd Gnd nmos l = 45n w = 180n
ENDS
*****
* NAND
.SUBCKT NAND A B OUT
 *** P-MOS
 m0 OUT A VDD
               VDD pmos l = 45n w = 360n
         VDD
 ml OUT B
               VDD
                   pmos 1 = 45n w = 360n
 *** NMOS
 m2 OUT A x Gnd
m3 x B Gnd Gnd
               Gnd nmos l = 45n w = 180n
Gnd nmos l = 45n w = 180n
.ENDS
*****
* NAND3
.SUBCKT NAND3 A B C OUT
 *** P-MOS
 m0 OUT A
          VDD
               VDD
                   pmos 1 = 45n w = 360n
 m1 OUT B
          VDD
               VDD
                   pmos 1 = 45n w = 360n
                   pmos l = 45n w = 360n
 m2 OUT C VDD
               VDD
 *** NMOS
 m3 OUT A x
m4 x B y
               Gnd
                   nmos l = 45n w = 180n
                   nmos l = 45n w = 180n
               Gnd
 m5 y
      C Gnd Gnd
                   nmos l = 45n w = 180n
.ENDS
*****
* NAND4
* * * * * * * * * * * * *
            ****
.SUBCKT NAND4 A B C D OUT
 *** P-MOS
 m0 OUT A
          VDD
               VDD
                    pmos l = 45n w = 360n
 ml OUT B
          VDD
               VDD
                   pmos 1 = 45n w = 360n
 m2 OUT C
          VDD
               VDD
                   pmos 1 = 45n w = 360n
 m3 OUT D
                   pmos 1 = 45n w = 360n
         VDD
               VDD
 *** NMOS
 m4 OUT A
                   nmos l = 45n w = 180n
               Gnd
          х
 m5 x B
                   nmos l = 45n w = 180n
          y
z
               Gnd
                   nmos l = 45n w = 180n
 m6 y C
               Gnd
                   nmos 1 = 45n w = 180n
 m7zD
          Gnd
               Gnd
. ENDS
*****
* NAND5
*******
.SUBCKT NAND5 A B C D E OUT
 *** P-MOS
                    pmos 1 = 45n w = 360n
 m0 OUT A
          VDD
               VDD
                    pmos \ l = 45n \ w = 360n
 ml OUT B
          VDD
               VDD
                    pmos 1 = 45n w = 360n
 m2 OUT C
          VDD
               VDD
                   pmos l = 45n w = 360n
pmos l = 45n w = 360n
 m3 OUT D
          VDD
               VDD
 m4 OUT E
         VDD
               VDD
 *** NMOS
 m5 OUT A
          W
               Gnd
                   nmos l = 45n w = 180n
                   nmos l = 45n w = 180n
 m6w B
          х
               Gnd
 m7 x C
               Gnd
                   nmos 1 = 45n w = 180n
          У
                   nmos l = 45n w = 180n
 m8y D
               Gnd
 m9 z E Gnd Gnd nmos l = 45n w = 180n
.ENDS
```

```
**********
* AND
.SUBCKT AND A B OUT
Xnand A B x NAND
Xinv x OUT INV
.ENDS
*****
* AND3
*****
.SUBCKT AND3 A B C OUT
 Xnand3 A B C x NAND3
 Xinv
    x OUT INV
.ENDS
*****
* AND4
*****
.SUBCKT AND4 A B C D OUT
 Xnand4 A B C D x
                NAND4
            OUT
                INV
 Xinv x
.ENDS
*****
* AND5
*****
.SUBCKT AND5 A B C D E OUT
Xnand5 A B C D E x
               NAND5
 Xinv x
            OUT
                INV
.ENDS
*****
* XOR
*****
.SUBCKT XOR A B OUT
 *** A' ***
    A_NOT
 m0
         А
             VDD
                 VDD pmos 1 = 45n w = 360n
                 Gnd nmos 1 = 45n w = 180n
 m2
    A_NOT
         А
             Gnd
 *** B' ***
   B_NOT B
B_NOT B
             VDD
                 VDD pmos l = 45n w = 360n
 m1
                 Gnd nmos 1 = 45n w = 180n
 m 3
             Gnd
 *** XOR ***
 *** P-MOS
 m4
    OUT
        А
             W
                 VDD pmos 1 = 45n w = 360n
                 VDD pmos 1 = 45n w = 360n
        A_NOT
 m5
    OUT
             x
                 VDD pmos 1 = 45n w = 360n
             VDD
 m6
    W
        B_NOT
                 VDD pmos 1 = 45n w = 360n
       В
 m7
    х
             VDD
 *** NMOS
        A
    У
                 Gnd nmos 1 = 45n w = 180n
 m8
             Gnd
 m9
     z
        A_NOT
             Gnd
                 Gnd nmos 1 = 45n w = 180n
                 Gnd nmos l = 45n w = 180n
 m10
    OUT
        В
             У
                 Gnd nmos 1 = 45n w = 180n
    OUT B_NOT
 m11
              z
.ENDS
*****
* NOR
*****
.SUBCKT NOR A B OUT
 *** NMOS
 m0 OUT A
        Gnd
            Gnd
                nmos l = 45n w = 180n
ml OUT B Gnd
                nmos l = 45n w = 180n
            Gnd
 *** P-MOS
                pmos 1 = 45n w = 360n
 m2 OUT A
            VDD
        х
 m3 x B VDD VDD pmos 1 = 45n w = 360n
.ENDS
*****
* NOR3
*****
.SUBCKT NOR3 A B C OUT
 *** NMOS
 m0 OUT A
        Gnd
            Gnd
                nmos l = 45n w = 180n
ml OUT B Gnd
                nmos l = 45n w = 180n
            Gnd
m2 OUT C
        Gnd
            Gnd
                nmos l = 45n w = 180n
 *** P-MOS
 m3 OUT A
            VDD pmos 1 = 45n w = 360n
        х
               pmos 1 = 45n w = 360n
 m4 x
     В
            VDD
        V
```

```
C VDD VDD pmos l = 45n w = 360n
m5 y
. ENDS
*****
* NOR4
.SUBCKT NOR4 A B C D OUT
 *** NMOS
 m0 OUT A
        Gnd
            Gnd
                nmos l = 45n w = 180n
                nmos l = 45n w = 180n
nmos l = 45n w = 180n
 ml OUT B
        Gnd
            Gnd
 m2 OUT C
        Gnd
            Gnd
m3 OUT D Gnd
            Gnd
                nmos 1 = 45n w = 180n
 *** P-MOS
 m4 OUT A
        х
            VDD
                pmos l = 45n w = 360n
                pmos 1 = 45n w = 360n
 m5 x B y
            VDD
                pmos 1 = 45n w = 360n
 m6 y
      С
        Z
            VDD
     D VDD
 m7 z
            VDD
                pmos l = 45n w = 360n
.ENDS
*****
* NOR5
*****
.SUBCKT NOR5 A B C D E OUT
 *** NMOS
 m0 OUT A
        Gnd
            Gnd
                nmos l = 45n w = 180n
 m1 OUT B
        Gnd
            Gnd
                nmos l = 45n w = 180n
                nmos l = 45n w = 180n
 m2 OUT C Gnd
            Gnd
               nmos 1 = 45n w = 180n
nmos 1 = 45n w = 180n
nmos 1 = 45n w = 180n
 m3 OUT D
        Gnd
            Gnd
m4 OUT E Gnd
            Gnd
 *** P-MOS
 m5 OUT A
        W
           VDD
              pmos 1 = 45n w = 360n
 m6w B
        x VDD
               pmos 1 = 45n w = 360n
     C y VDD
D z VDD
 m7 x
               pmos 1 = 45n w = 360n
 m8 y
               pmos 1 = 45n w = 360n
               pmos 1 = 45n w = 360n
     E VDD VDD
 m9 z
.ENDS
*****
* OR
*****
.SUBCKT OR A B OUT
Xnor A B x NOR
Xinv x OUT INV
.ENDS
*****
* OR3
****
.SUBCKT OR3 A B C OUT
Xnor3 A B C x NOR3
Xinv x OUT INV
ENDS
*****
* OR4
*****
.SUBCKT OR4 A B C D OUT
Xnor4 A B C D x
Xinv x OUT
                NOR4
               INV
ENDS
*****
* OR5
*****
.SUBCKT OR5 A B C D E OUT
 Xnor5 A B C D E x NOR5
Xinv x OUT INV
.ENDS
*****
* CLA Full-Adder
*****
   A ----|
                           хI
           1
    | XOR |-----x---
                            | XOR |--- S
   B -----|
                          Cin
         ΑI
                                1
                            | AND |--- G
* Cin -----
                            BI
                               AI
                               1
                            | OR |--- P
                            BI
```

```
****************
.SUBCKT CLA_FULL_ADDER A B CIN S G P
 Xxor1 A B x XOR
 Xxor2 x CIN S XOR
Xand A B G AND
Xor A B P OR
 Xor
.ENDS
*****
* CLA
*****
.SUBCKT CLA AO A1 A2 A3 BO B1 B2 B3 CIN SO S1 S2 S3 COUT
*** Bit 0 ***
 Xfull_adder0 A0 B0 CIN S0 G0 P0 CLA_FULL_ADDER
*** Bit 1 ***
* C1 = G0 + (P0 * CIN)
 Xand1 PO CIN
                         X1 AND
 Xor1
              G0 X1
                          C1
                                    OR
 Xfull_adder1 A1 B1 C1 S1 G1 P1 CLA_FULL_ADDER
*** Bit 2 ***
* C2 = G1 + (G0 * P1) + (CIN * P0 * P1)
           CIN PO P1 X2 AND3
 Xand2a
  Xand2b
              G0 P1
                          Y2
                                   AND
 Xor2
              G1 X2 Y2
                        C2
                                   OR3
 Xfull_adder2 A2 B2 C2 S2 G2 P2 CLA_FULL_ADDER
*** Bit 3 ***
* C3 = G2 + (G1 * P2) + (G0 * P1 * P2) + (CIN * P0 * P1 * P2)
           CIN PO P1 P2 X3 AND4
 Xand3a
              G0 P1 P2
 Xand3b
                              YЗ
                                       AND 3
              G1 P2
                             Z3
 Xand3c
                                       AND
 Xor3
              G2 X3 Y3 Z3
                              C3
                                       OR4
                            S3 G3 P3 CLA_FULL_ADDER
 Xfull_adder3 A3 B3 C3
*** COUT ***
* C4 = G3 + (G2 * P3) + (G1 * P2 * P3) + (G0 * P1 * P2 * P3) + (CIN * P0 * P1 * P2 * P3)
            CIN P0 P1 P2 P3 W4 AND5
 Xand4a
  Xand4b
            G0 P1 P2 P3 X4
G1 P2 P3 Y4
                                   AND4
            G1 P2 P3
                                   AND 3
 Xand4c
 Xand4d
            G2 P3
                                   AND
                            7.4
                                  OR5
            G3 W4 X4 Y4 Z4 COUT
 Xor4
ENDS
******
* Test that FOUR_BIT_FULL_ADDER gate is correct
XCLA AO A1 A2 A3 BO B1 B2 B3 CIN SO S1 S2 S3 COUT CLA
* Add capacitors
C0 S0 Gnd 10f
C1 S1 Gnd 10f
C2 S2 Gnd 10f
C3 S3 Gnd 10f
Ccout COUT Gnd 10f
* SYNTAX: V <name> <node1> <node2> pulse( <value1>, <value2>, <delay>,<rise time>, <fall time>, <ON time>, <period>)
*** define input signals for A and B PULSE
                                            1n, 0.001u, 0.001u, 7.999u,
     VAO
          AÖ
                Gnd pulse( 0, 1.8V,
                                                                                 1611)
                                     1.8V,
     VA1
          A1
                Gnd
                     pulse( 0,
                                                                                 16u '
     VA2
           A2
                Gnd
                     pulse( 0,
                                     1.8V,
                                                                                 1611
                     pulse( 0,
                                     1.8V,
     VA3
          A3
                Gnd
                                                                                 16u
                                     0V,
0V,
     VB0
           в0
                Gnd
                      pulse( 1.8V,
                                                                                 16u
                                             1n, 0.001u,
1n, 0.001u,
1n, 0.001u,
1n, 0.001u,
1n, 0.001u,
     VB1
           В1
                     pulse( 1.8V,
                                                              0.001u, 7.999u,
                Gnd
                                                                                 16u
                     pulse( 1.8V,
     VB2
           В2
                Gnd
                                      0V,
                                                              0.001u,
                                                                        7.999u,
                                                                                 16u )
     VB3 B3
                     pulse( 1.8V,
                                      0V,
                                                              0.001u,
                                                                       7.999u,
                Gnd
                                                                                 16u )
                                                                      3.999u,
     VCIN CIN
                Gnd
                      pulse( 1.8V,
                                      0V,
                                                              0.001u,
                                                                                 8u )
* SYNTAX .TRAN <time step> <final time>
.TRAN 0.049u 17u
.MEASURE FALL_DELAY
 +TRIG V(CIN) VAL='Supply/2' FALL = 1
  +TARG V(COUT) VAL='Supply/2' FALL = 1
.MEASURE RISE_DELAY
 +TRIG V(CIN) VAL='Supply/2' RISE = 2
  +TARG V(COUT) VAL='Supply/2' RISE = 2
* .MEASURE TRAN lowtohigh AVG i(VDD) FROM=3.99u TO=4.01u
* .MEASURE TRAN low AVG i(VDD) FROM=3.97u TO=3.99u
* .MEASURE TRAN hightolow AVG i(VDD) FROM=7.99u TO=8.01u
* .MEASURE TRAN high AVG i(VDD) FROM=7.97u TO=7.99u
```

- * * .MEASURE TRAN supplycurrent AVG i(VDD) FROM=3.99u TO=4.01u
 * .MEASURE TRAN lowtohighpower PARAM='-lowtohigh * 0.6' **0.6 is supply voltage
 * .MEASURE TRAN lowpower PARAM='-low * 0.6' **0.6 is supply voltage
 * .MEASURE TRAN hightolowpower PARAM='-hightolow * 0.6' **0.6 is supply voltage
- * .MEASURE TRAN highpower PARAM='-high * 0.6' **0.6 is supply voltage

.TEMP 90

.OPTION Post

.end

APPENDIX D COSMOSSCOPE WAVEFORMS

A. RCA Waveforms

The following three waveforms are from the same simulation for the RCA. Waveforms 1, 2, and 3 in this section show the four-bit input A, four-bit input B as well as the CIN bit, and four-bit output sum and one-bit COUT result respectively. The waveforms are the results of two test cases:

Test Case	Innut A	Input B	CIN	Test Begin	Test End	
Test Cuse	input 11		CITY	micro-seconds		
1	1111	0001	0	0.0	0.4	
2	1110	0001	0	0.4	0.8	

1) RCA Simulation: Waveform of the Four-Bit Input A



2) RCA Simulation: Waveform of the Four-Bit Input B and One-Bit CIN





3) RCA Simulation: Waveform of the Four-Bit Output Sum and One-Bit COUT

B. CLA Waveforms

The following three waveforms are from the same simulation for the CLA. Waveforms 1, 2, and 3 in this section show the four-bit input A, four-bit input B as well as the CIN bit, and four-bit output sum and one-bit COUT result respectively. The waveforms are the results of two test cases:

Test Case	Input A	Input B	CIN	Test Begin Test End micro-seconds			
1	1111	0001	0	0.0	0.4		
2	1110	0001	0	0.4	0.8		

1) CLA Simulation: Waveform of the Four-Bit Input A





2) CLA Simulation: Waveform of the Four-Bit Input B and One-Bit CIN

3) CLA Simulation: Waveform of the Four-Bit Output Sum and One-Bit COUT

